

ABSTRACT OF THE DISCLOSURE:

In a solid-state imaging device, a plurality of vertical charge transfer paths is arranged at a horizontal pitch A within a photoelectric conversion region, and at a pitch B that is smaller than the pitch A in a portion where the signals are input into the horizontal charge transfer path. A read-out amplifier and a horizontal charge transfer path for receiving signals from vertical charge transfer paths are provided for each photoelectric conversion block into which the photoelectric conversion region has been partitioned. The read-out amplifiers have the same shape and their positional relation is one of parallel displacement in regions that are obtained by changing the pitch of the vertical charge transfer portions. Thus, a solid-state imaging device is achieved that is not so easily influenced by mask misalignments or skewed ion implantation angles, and in which signal read-out at high speeds is possible.

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